

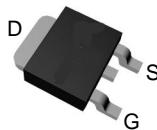
# SM1A16PSU/UB

## P-Channel Enhancement Mode MOSFET

### Features

- 100V/-13A,
- $R_{DS(ON)}=205\text{m}\Omega$  (max.) @  $V_{GS}=-10\text{V}$
- $R_{DS(ON)}=300\text{m}\Omega$  (max.) @  $V_{GS}=-4\text{V}$
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- 100% UIS +  $R_g$  Tested

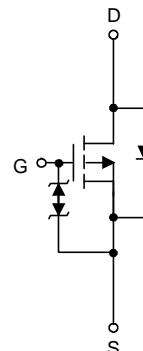
### Pin Configuration



Top View of TO-252-2



Top View of TO-251

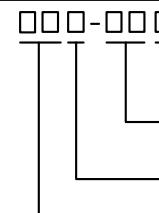
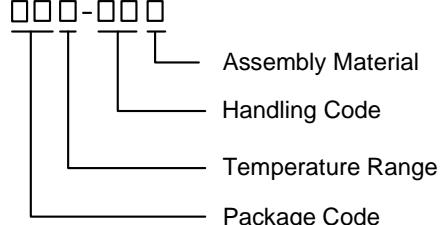
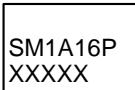


P-Channel MOSFET

### Applications

- Power Management in Desktop Computer or DC/DC Converters.

### Ordering and Marking Information

SM1A16PS  	Package Code U : TO-252-2   UB : TO-251 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel for TO-252-2 Package TU : Tube for TO-251 Package Assembly Material G : Halogen and Lead Free Device
SM1A16PS   U/UB : 	XXXXX - Lot Code

# SM1A16PSU/UB

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## Absolute Maximum Ratings

Symbol	Parameter	Rating		Unit
<b>Common Ratings</b> ( $T_A = 25^\circ\text{C}$ Unless Otherwise Noted)				
$V_{DSS}$	Drain-Source Voltage	-100	$\text{V}$	
$V_{GSS}$	Gate-Source Voltage	$\pm 20$		
$T_J$	Maximum Junction Temperature	150	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$	
$I_S$	Diode Continuous Forward Current	-1	$\text{A}$	
$I_{DP}$	300 $\mu\text{s}$ Pulse Drain Current Tested	$T_C = 25^\circ\text{C}$	-52	$\text{A}$
		$T_C = 100^\circ\text{C}$	-32	
$I_D$	Continuous Drain Current	$T_C = 25^\circ\text{C}$	-13*	$\text{A}$
		$T_C = 100^\circ\text{C}$	-8	
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	50	$\text{W}$
		$T_C = 100^\circ\text{C}$	20	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	2.5	$^\circ\text{C}/\text{W}$	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	50	$^\circ\text{C}/\text{W}$	

Note : \* Current limited by bond wire.

## Electrical Characteristics

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Test Conditions	SM1A16PSU/UB			Unit
			Min.	Typ.	Max.	
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$ , $I_{DS}=-250\mu\text{A}$	-100	-	-	$\text{V}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-80\text{V}$ , $V_{GS}=0\text{V}$	-	-	-1	$\mu\text{A}$
		$T_J=85^\circ\text{C}$	-	-	-30	
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{DS}=-250\mu\text{A}$	-1	-	-3	$\text{V}$
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 16\text{V}$ , $V_{DS}=0\text{V}$	-	-	$\pm 10$	$\mu\text{A}$
$R_{DS(\text{ON})}^{\text{a}}$	Drain-Source On-state Resistance	$V_{GS}=-10\text{V}$ , $I_{DS}=-7.8\text{A}$	-	-	205	$\text{m}\Omega$
		$V_{GS}=-4\text{V}$ , $I_{DS}=-6\text{A}$	-	-	300	
<b>Diode Characteristics</b>						
$V_{SD}^{\text{a}}$	Diode Forward Voltage	$I_{SD}=-1\text{A}$ , $V_{GS}=0\text{V}$	-	-0.75	-1.1	$\text{V}$
$t_{rr}$	Reverse Recovery Time	$I_{DS}=-7.8\text{A}$ , $dI_{SD}/dt=100\text{A}/\mu\text{s}$	-	34	-	$\text{ns}$
Qrr	Reverse Recovery Charge		-	59	-	$\text{nC}$

# SM1A16PSU/UB

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## Electrical Characteristics (Cont.) ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	SM1A16PSU/UB			Unit
			Min.	Typ.	Max.	
<b>Dynamic Characteristics <sup>b</sup></b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0V$ , $V_{DS}=-30V$ , Frequency=1.0MHz	-	1050	-	pF
$C_{oss}$	Output Capacitance		-	70	-	
$C_{rss}$	Reverse Transfer Capacitance		-	40	-	
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=-30V$ , $R_L=30\Omega$ , $I_{DS}=-1A$ , $V_{GEN}=-10V$ , $R_G=6\Omega$	-	11	21	ns
$t_r$	Turn-on Rise Time		-	10	19	
$t_{d(OFF)}$	Turn-off Delay Time		-	55	100	
$t_f$	Turn-off Fall Time		-	30	55	
<b>Gate Charge Characteristics <sup>b</sup></b>						
$Q_g$	Total Gate Charge	$V_{DS}=-50V$ , $V_{GS}=-10V$ , $I_{DS}=-7.8A$	-	20.9	38	nC
$Q_{gs}$	Gate-Source Charge		-	4.2	-	
$Q_{gd}$	Gate-Drain Charge		-	5.2	-	

Note a : Pulse test ; pulse width $\leq 300\mu\text{s}$ , duty cycle $\leq 2\%$ .

Note b : Guaranteed by design, not subject to production testing.

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## Typical Operating Characteristics

